

**AMENDMENTS TO THE SPECIFICATION**

(1) Please amend the title of the invention, on page 1, to read as follows:

**METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE**

(2) Please insert the following new sentence at line 5 on page 1:

This application is a continuation of co-pending application serial number 9/939,801, which was filed on august 28, 2001.

(3) Please delete the ABSTRACT OF THE DISCLOSURE, appearing on a separate sheet at the end of the Specification, and replace it with the following:

A method for manufacturing a semiconductor device according to the present invention includes preparing a first semiconductor chip having a semiconductor substrate area that is free of the formation of transistors that generate heat when in operation, and a transistor forming area that surrounds the semiconductor substrate area, and mounting a second semiconductor chip on the first semiconductor chip so as to arrange the second semiconductor chip just above the substrate area of the first semiconductor chip. The method also includes connecting at least one first electrode formed on the periphery of the semiconductor substrate area with at least one first metal wire to at least one third electrode on the second semiconductor chip, and connecting at least one second electrode formed on the periphery of the transistor forming area with at least one second metal wire to a plurality of leads disposed around the first semiconductor chip.